Application No.	Applicant(s)
10/805,880	SHAH ET AL.
Examiner	Art Unit
Igwe U. Anya	2825
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of this communication to file a reply	national stage application from the
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 6. CORRECTED DRAWINGS (as "replacement sheets") must be submitted. (a) including changes required by the Notice of Draftsperson's Patent Drawing Review (PTO-948) attached 1) hereto or 2) to Paper No./Mail Date (b) including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No./Mail Date Identifying indicia such as the application number (see 37 CFR 1.84(c)) should be written on the drawings in the front (not the back) of each sheet. Replacement sheet(s) should be labeled as such in the header according to 37 CFR 1.121(d). 7. DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL. 	
6. ☐ Interview Summary Paper No./Mail Da 8), 7. ☐ Examiner's Amend	ate ^
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Allowable Subject Matter

1. The following is an examiner's statement of reasons for allowance: Applicant's claims 9, 17, and 19 are allowable, because prior art does not teach inter alia:

(claims 9, 17) applying a plasma etch to a first part of a metal layer, and applying a wet etch to etch a second part of the metal layer, a dielectric layer and a sacrificial layer; and

(claim 19) a conformal depositing of a sacrificial layer selected from silicon nitride, carbon doped silicon nitride and silicon dioxide on a patterned polysilicon and third exposed parts of a second metal layer, removing the sacrificial layer on the third exposed parts of the second metal layer, and removing the exposed third parts of the second metal layer and an underlying part of a first metal layer.

2. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Remarks

3. The examiner has reviewed prior art in light of applicant's comments and amendment and finds it persuasive as to the reading prior art.

Contact Information

4. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Igwe U. Anya whose telephone number is (571) 272-1887. The examiner can normally be reached on M - F 8:30am - 5:00pm.

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872-9306.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Matthew S. Smith can be reached on (571) 272-1907. The fax phone number for the organization where this application or proceeding is assigned is 703-

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Igwe U. Anya Examiner Art Unit 2825

IA

October 28, 2004

MATTHEW SMITH SUPERVISORY PATENT EXAMINER TECHNOLOGY CENTER 2800